

**FABRICATION OF NITROGEN DETECTOR FROM POROUS
SILICON NANOSTRUCTURES**

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**Final Year Project Report Submitted in
Partial Fulfillment of the Requirement for the
Degree of Bachelor of Science (Hons.) Industrial Physics
in the Faculty of Applied Sciences
Universiti Teknologi MARA**

JANUARY 2012

ACKNOWLEDGEMENTS

While preparing this report, I have got support from many persons helping to arrange and compiling the report. Firstly, I wish to express my sincere appreciation to my supervisor, Prof. Dr. Saifollah Bin Abdullah for his invaluable assistance and guidance. Secondly, special thanks to Co-Supervisor, Assoc. Prof. Dr. Mohamad Rusop Bin Mahmood for his guidance and support to proficiently transforming my idea to written document. Thanks to my friends and my parents because the following people contributed greatly to this report and I am grateful to each of them. Last but never least, thanks to my senior, Mohd Hushairi and laboratory assistant Mr Azlan Jaafar because of their patience cooperation and spirit de corps to make sure this report will be submitted at the punctual time.

Norhayati Bt.Othman

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ABSTRACT

Nowadays, nanoscience there is an increasing demand for low-dimensional and nanostructure systems. Silicon is the most dominant material used in semiconductor technology but bulk silicon is not taken into consideration to used. Porous silicon is a potential candidate for various applications to fabricate miniaturized and cheap devices. The high surface area of this material such as porous silicon nanostructures makes it is widely used in fields of optics, detector technology and biomedicine. One of the main application areas of porous silicon is detector technology. In this study, the nitrogen detector is fabricated to determine the leakage of this gas where it can give harmful to people, animals and plants.

In this study the porous silicon nanostructure is fabricated by using anodization method because of simple and easy to handle. This method using HF 48% and the ethanol in etching process to etch the silicon bulk to be porous silicon with 20 mA/cm² of current density and the etching time is from 10 minutes - 40 minutes. The properties of the porous silicon nanostructure analyzed using I-V testing (electrical properties) and photoluminescence spectroscopy (optical properties). From the I-V testing, I-V graph obtained to analyze the sensitivity of the detection of the nitrogen gas and from the testing gained that the most sensitive sample to detect the existence of N₂ is sample P*Si*E40 where the sensitivity is 75 % for nitrogen flow rate at 2 bubbles per second in 10 seconds. 25.4% is a sensitivity of P*Si*E40 at 10 seconds exposure time where the flow rate is 5 bubbles per seconds 29.9% is sensitivity of the P*Si*E40 at 50 seconds exposure time with 5 bubbles per seconds as a reading of the gas flow rate.

For photoluminescence (PL), the PL spectrum is analyzed based on the intensity and wavelength of the spectrum to determine the pore size of the structure and to determine the energy band gap of the material. From the analysis, the result show that the PL wavelength is blue shift and sample PsiE20 got higher intensity compared to the others where the reading is 62.945444 a.u.